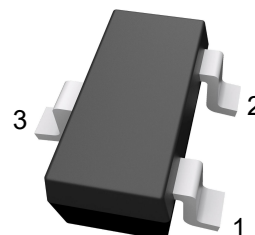


N-Channel Enhancement Mode Power MOSFET
Features

- High power and current handling capability
- $V_{DS} = 30V, I_D = 4A$
 $R_{DS(on)} < 45m\Omega @ V_{GS} = 10V$

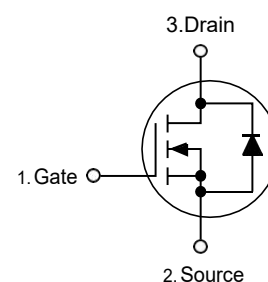
Application

- Load switch and in PWM applications
- Power management

SOT-23-3


1. Gate 2. Source 3. Drain

Marking Code:P2

Schematic Diagram

Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	4	A
Drain Current-Pulsed ^{Note1}	I_{DM}	16	A
Maximum Power Dissipation	P_D	1.3	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	96	°C/W
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PJM3402NSC

N-Channel Enhancement Mode Power MOSFET

Electrical Characteristics

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	30	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	--	--	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V	--	--	±100	nA
Gate Threshold Voltage ^{Note3}	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.5	--	1.4	V
Drain-Source On-Resistance ^{Note3}	R _{DS(on)}	V _{GS} =10V, I _D =4A	--	36	45	mΩ
		V _{GS} =4.5V, I _D =3A	--	39	50	mΩ
Forward Transconductance ^{Note3}	g _{FS}	V _{DS} =5V, I _D =1A	--	4	--	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1MHz	--	285	--	pF
Output Capacitance	C _{oss}		--	33	--	pF
Reverse Transfer Capacitance	C _{rss}		--	27	--	pF
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DS} =15V, I _D =2A, V _{GS} =4.5V, R _{GEN} =3Ω	--	15	--	nS
Turn-on Rise Time	t _r		--	42	--	nS
Turn-off Delay Time	t _{d(off)}		--	16	--	nS
Turn-off Fall Time	t _f		--	10	--	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =4A, V _{GS} =4.5V	--	2.6	--	nC
Gate-Source Charge	Q _{gs}		--	0.6	--	nC
Gate-Drain Charge	Q _{gd}		--	0.9	--	nC
Source-Drain Diode Characteristics						
Body Diode Forward Voltage ^{Note3}	V _{SD}	V _{GS} =0V, I _S =4A	--	--	1.2	V
Diode Forward Current ^{Note2}	I _S		--	--	4	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

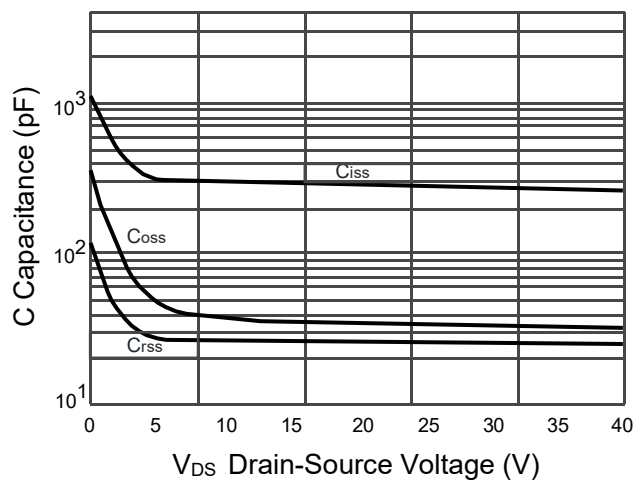
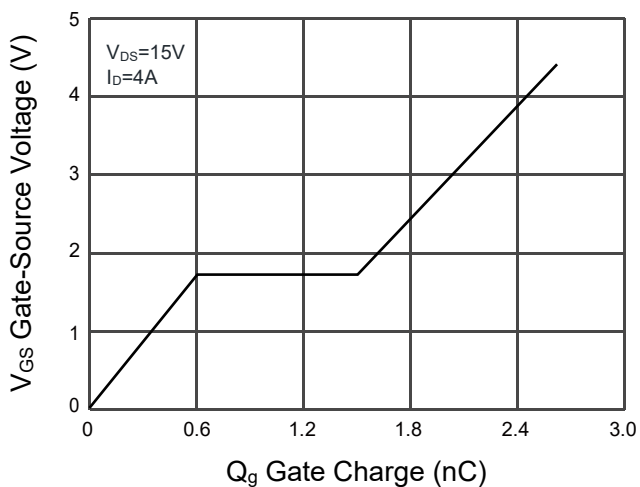
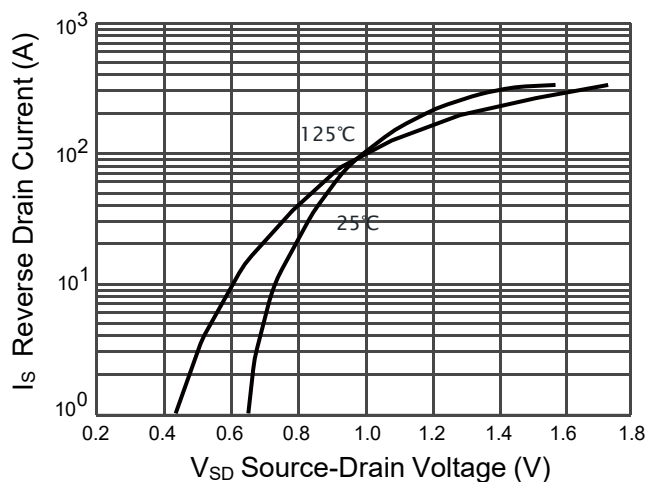
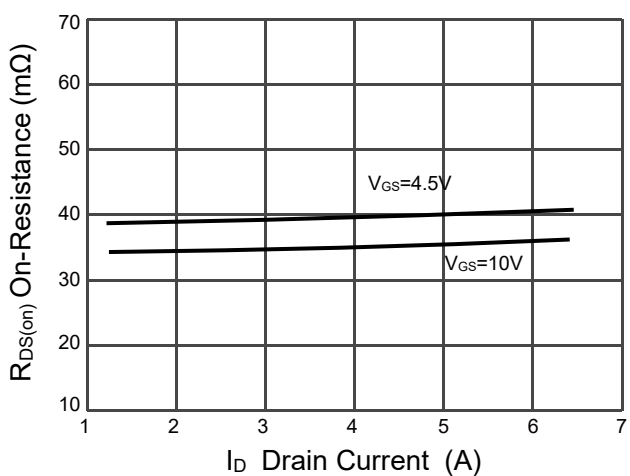
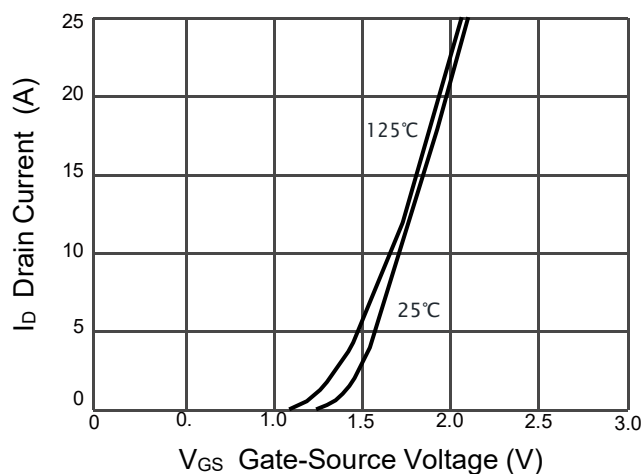
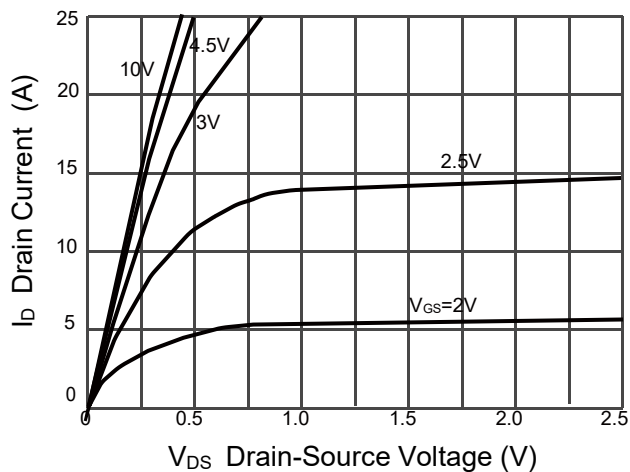
3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 0.5\%$.



PJM3402NSC

N-Channel Enhancement Mode Power MOSFET

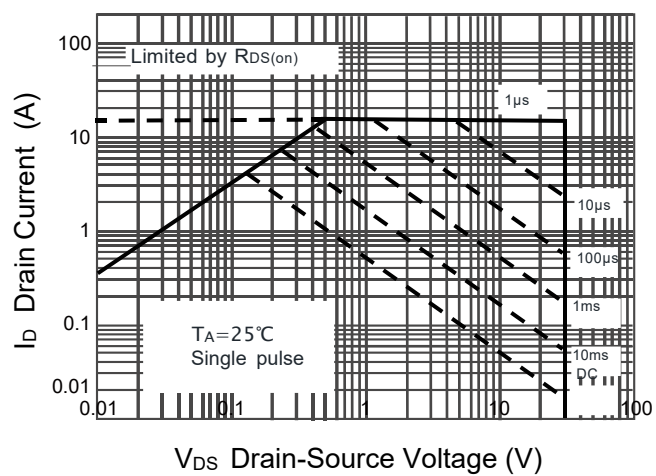
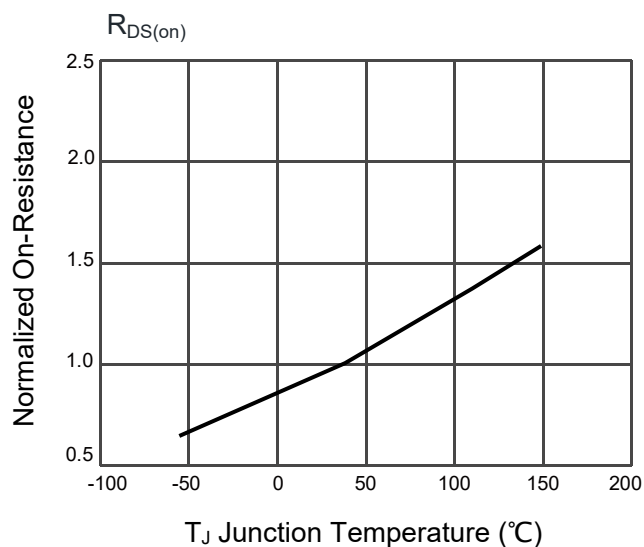
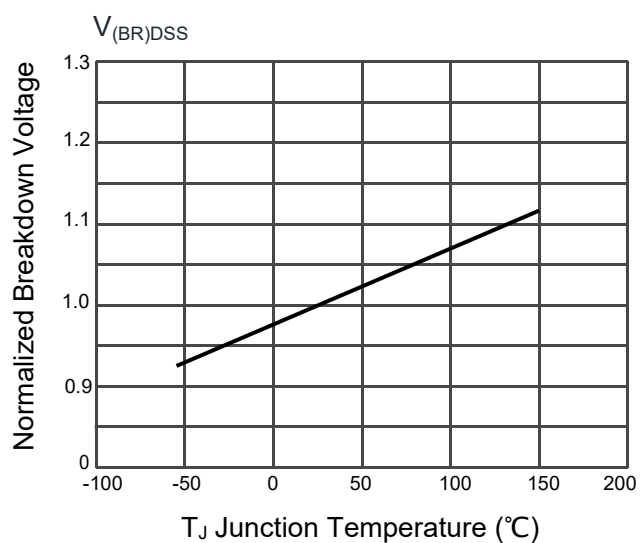
Typical Characteristic Curves





PJM3402NSC

N-Channel Enhancement Mode Power MOSFET





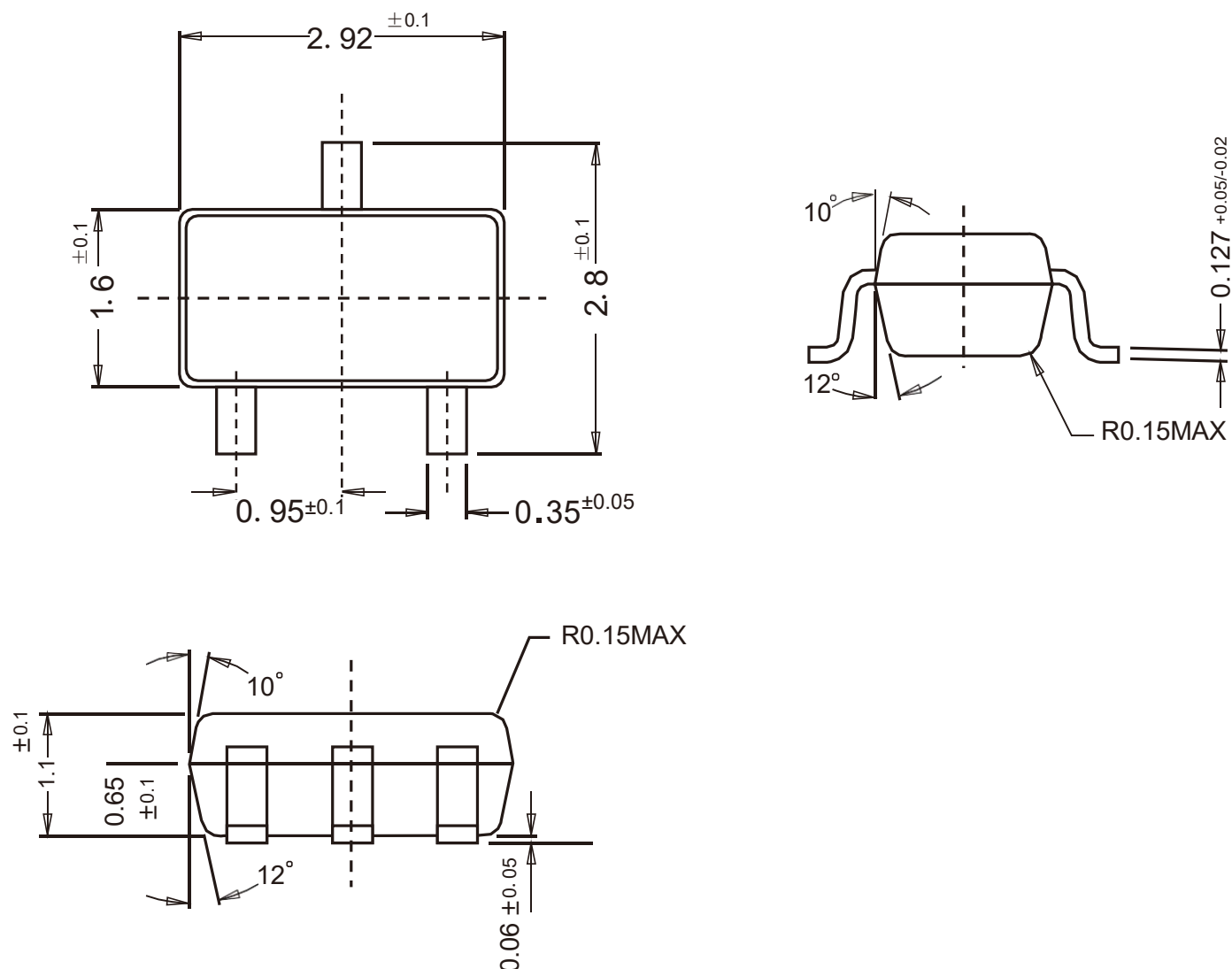
PJM3402NSC

N-Channel Enhancement Mode Power MOSFET

Package Outline

SOT-23-3

Dimensions in mm



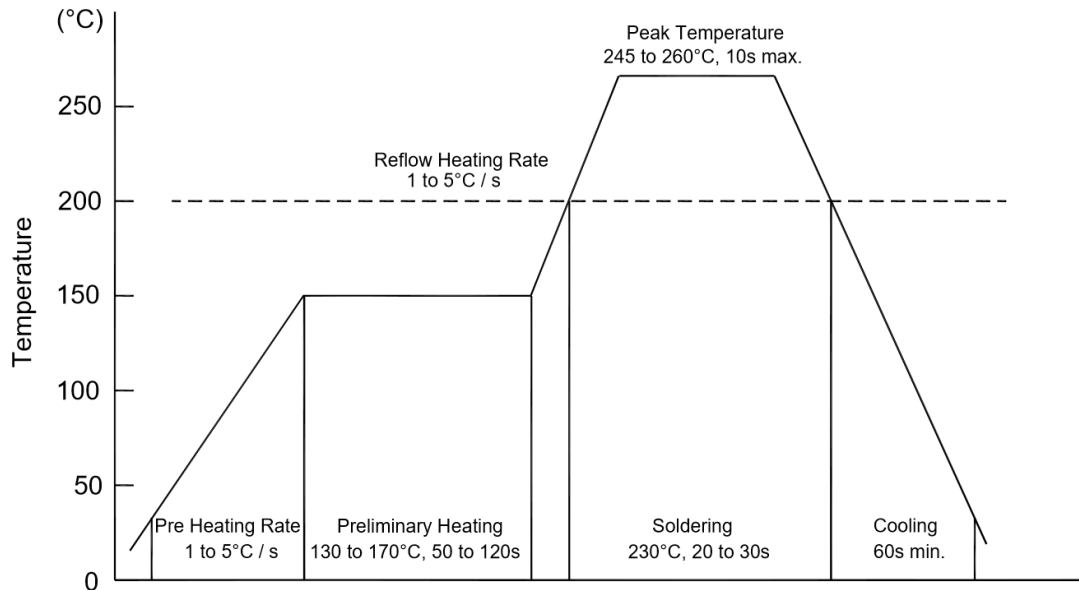
Ordering Information

Device	Package	Shipping
TN3402NSC	SOT-23-3	3,000PCS/Reel&7inches



Conditions of Soldering and Storage

◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245 °C. If peak temperature is below 245 °C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

◆ Conditions of hand soldering

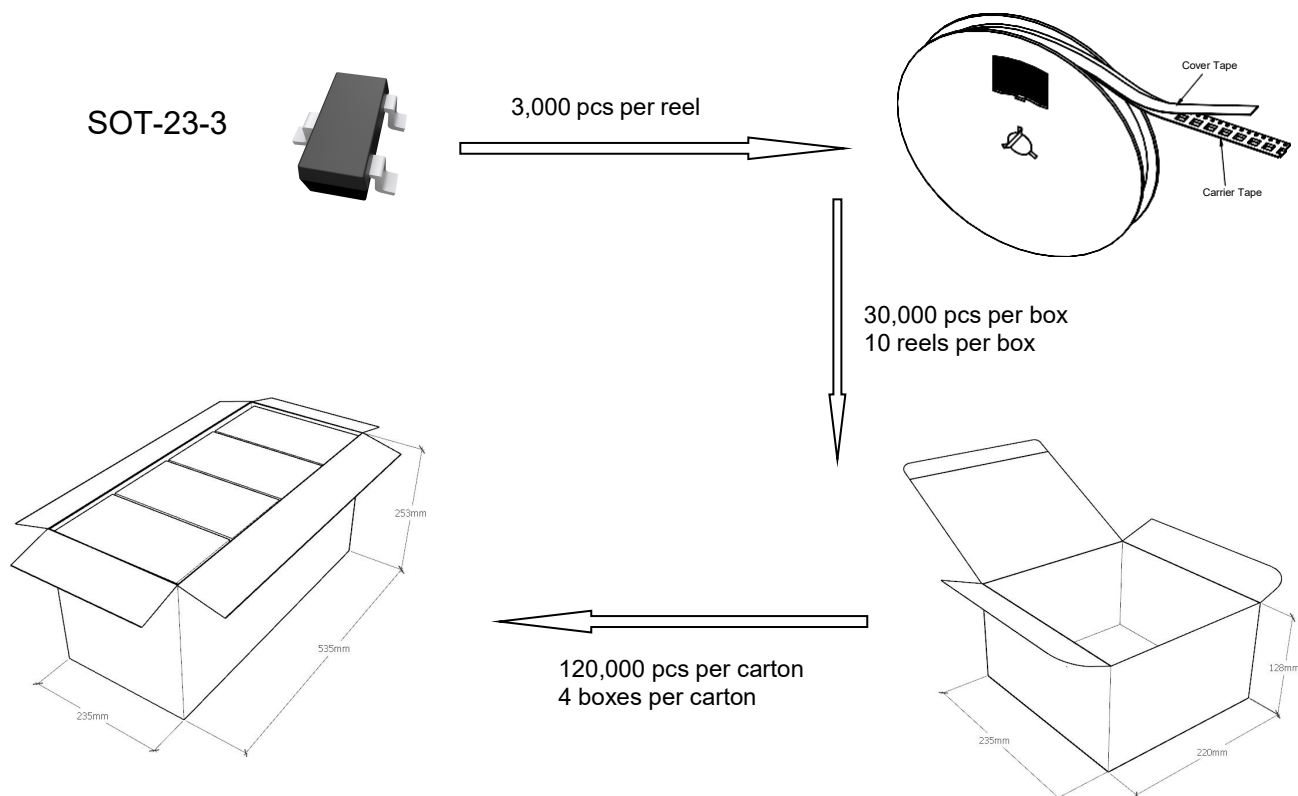
- Temperature: 370 °C
- Time: 3s max.
- Times: one time

◆ Storage conditions

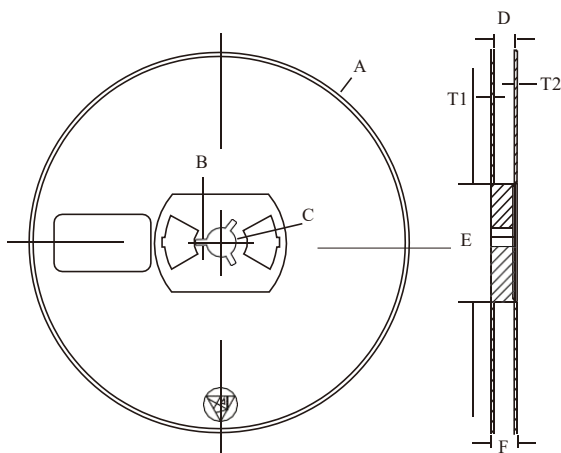
- **Temperature**
5 to 40 °C
- **Humidity**
30 to 80% RH
- **Recommended period**
One year after manufacturing

Package Specifications

- The method of packaging



◆ Embossed tape and reel data



Symbol	Value (unit: mm)
A	Ø 177.8±1
B	2.7±0.2
C	Ø 13.5±0.2
E	Ø 54.5±0.2
F	12.3±0.3
D	9.6+2/-0.3
T1	1.0±0.2
T2	1.2±0.2

Reel (7")

